

Features

- Uses CRM(CQ) advanced Trench MOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

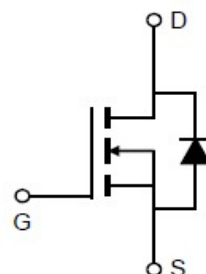
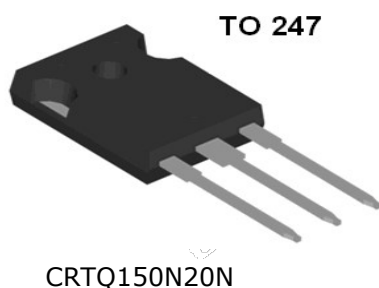
Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

Product Summary

V_{DS}	200V
$R_{DS(on)}$	13.3mΩ
I_D	92A

100% Avalanche Tested
100% DVDS Tested



Package Marking and Ordering Information

MARKING	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTQ150N20N	CRTQ150N20N	TO-247	Tube	N/A	N/A	25pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	92 160 58	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	368	A
Avalanche energy, single pulse ($L=1\text{mH}$, $R_g=25\Omega$)	E_{AS}	241	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	313	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.40	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	40	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	200	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	3	4	5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1 100	μA	$V_{DS}=200V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	± 1	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	13	16	mΩ	$V_{GS}=10V, I_D=30A$
Transconductance	g_{fs}	-	90	-	S	$V_{DS}=5V, I_D=30A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	7080	-	pF	$V_{GS}=0V, V_{DS}=100V,$ $f=1\text{MHz}$
Output Capacitance	C_{oss}	-	420	-		
Reverse Transfer Capacitance	C_{rss}	-	77	-		
Gate Total Charge	Q_G	-	123	-	nC	$V_{GS}=10V, V_{DS}=100V,$ $I_D=30A, f=1\text{MHz}$
Gate-Source charge	Q_{gs}	-	52	-		
Gate-Drain charge	Q_{gd}	-	35	-		
Turn-on delay time	$t_{d(on)}$	-	47	-	ns	$V_{GS}=10V, V_{DD}=100V,$ $R_{G_ext}=3\Omega$
Rise time	t_r	-	91	-		
Turn-off delay time	$t_{d(off)}$	-	100	-		
Fall time	t_f	-	70	-		
Gate resistance	R_G	-	5	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1\text{MHz}$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.8	1.3	V	$V_{GS}=0V, I_{SD}=30A$
Body Diode Continuous Forward Current	I_S			92	A	$T_C = 25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	129	-	ns	$I_F=30A,$ $dI/dt=100A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	830	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

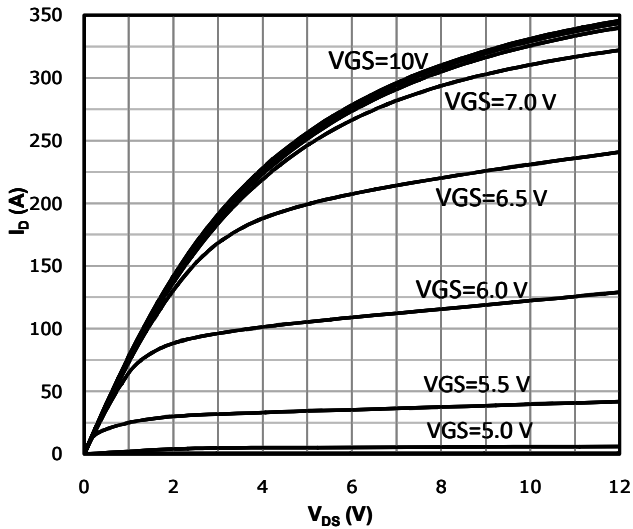


Fig 2: Transfer Characteristics

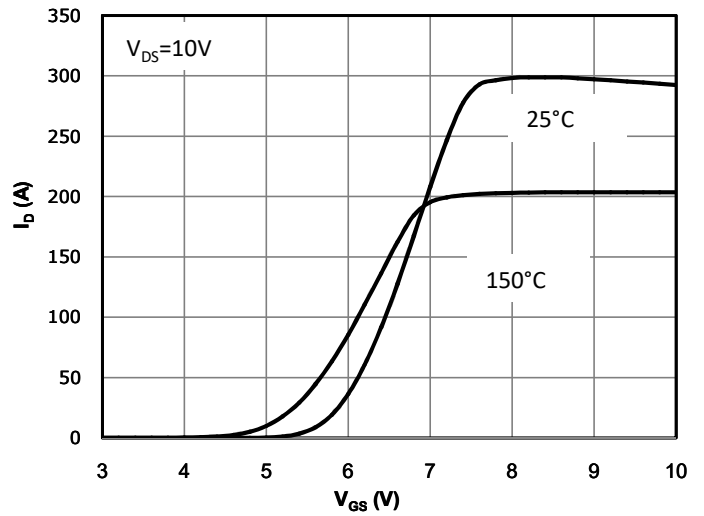


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

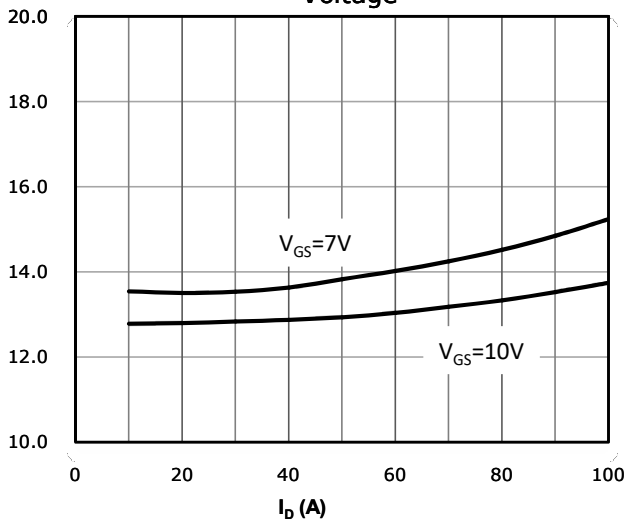


Fig 4: $R_{DS(on)}$ vs Gate Voltage

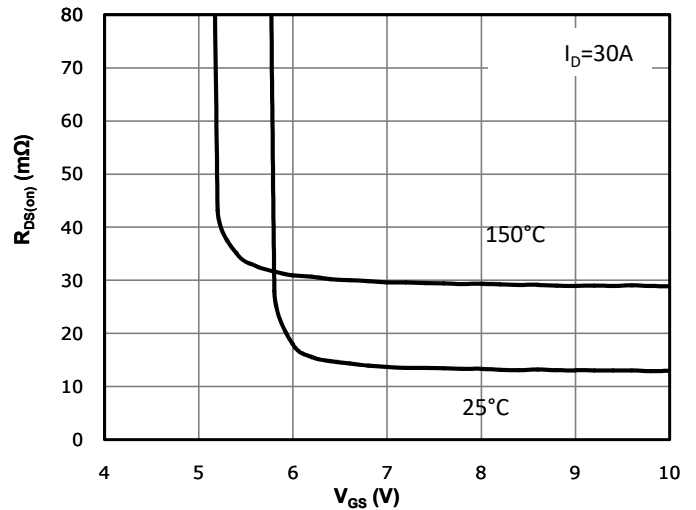


Fig 5: $V_{GS(th)}$ vs. Temperature

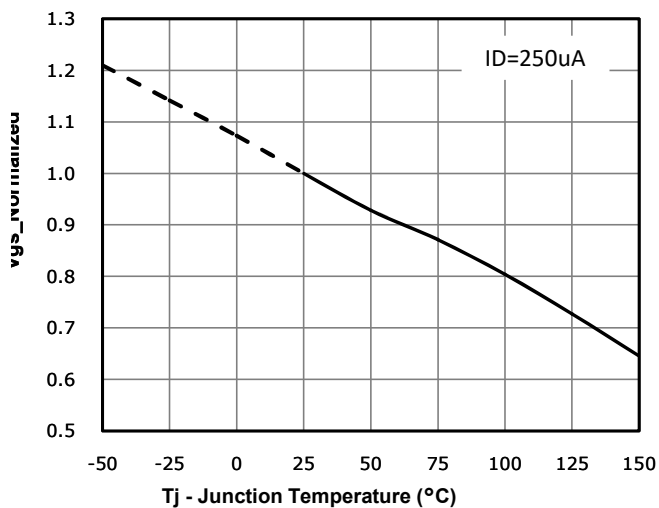


Fig 6: BVDSS vs. Temperature

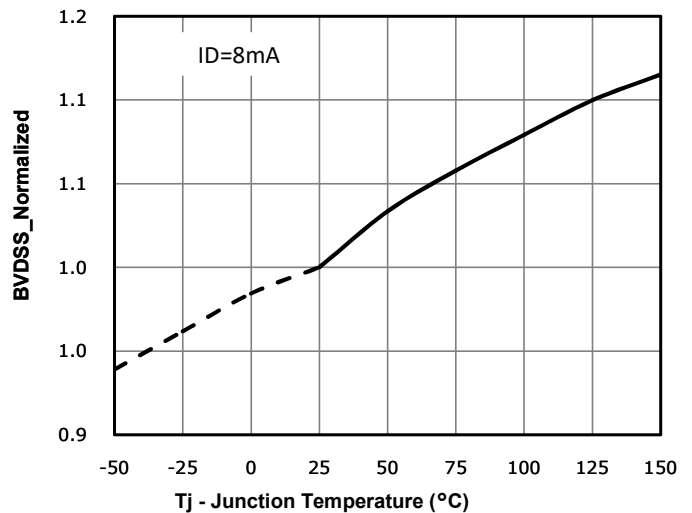


Fig 7: Rds(on) vs. Temperature

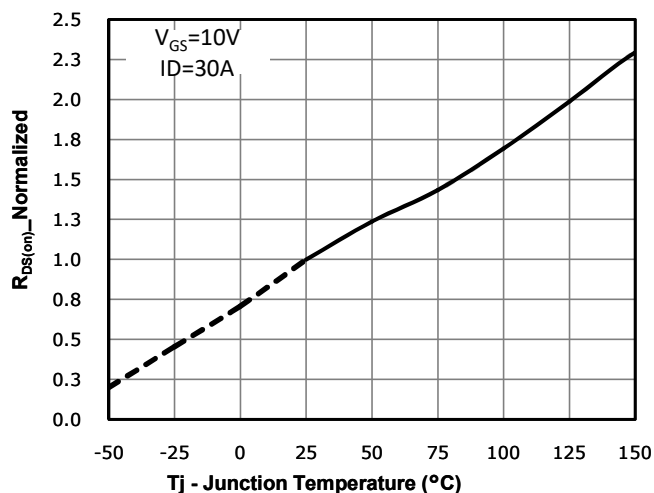


Fig 8: Capacitance Characteristics

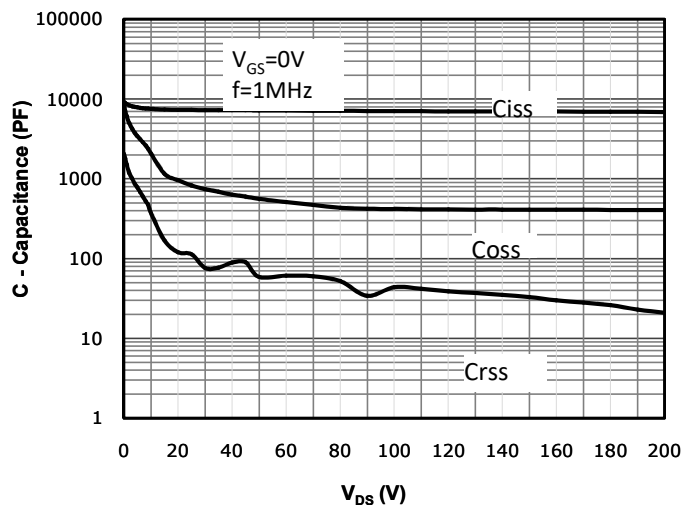


Fig 9: Gate Charge Characteristics

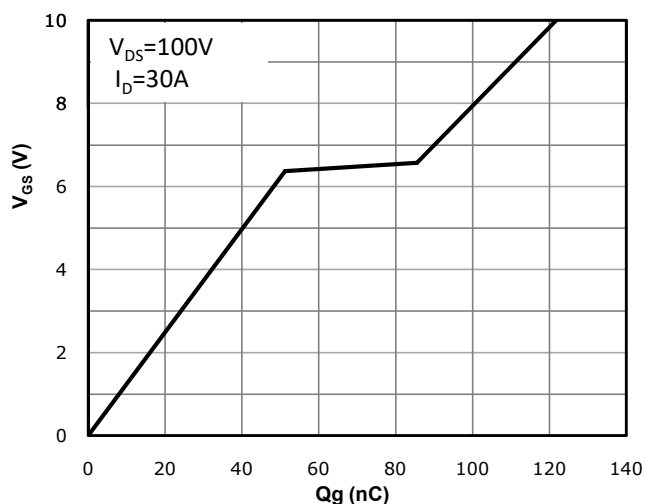


Fig 10: Body-diode Forward Characteristics

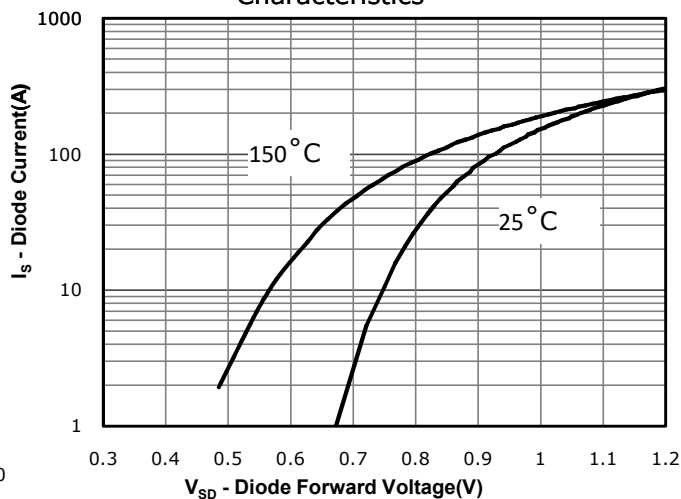


Fig 11: Power Dissipation

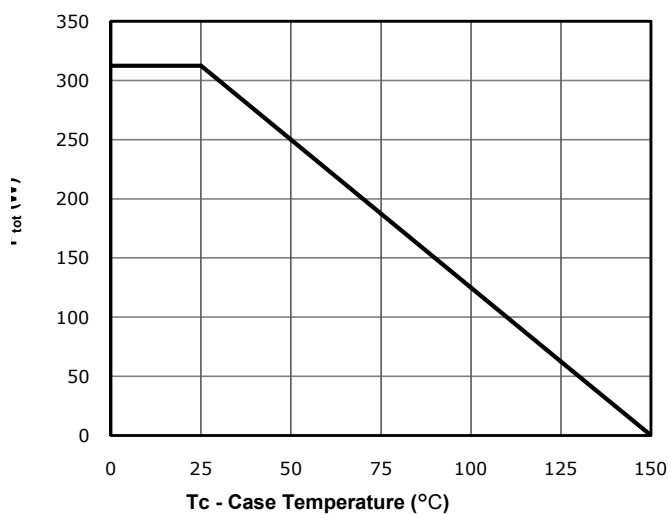


Fig 12: Drain Current Derating

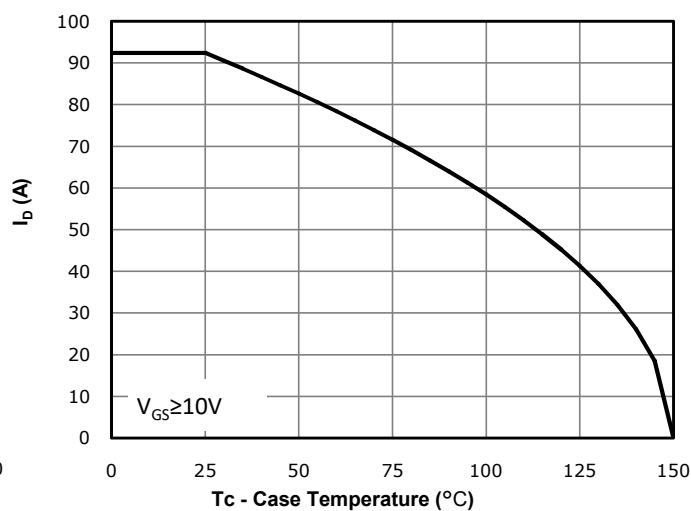


Fig 13: Safe Operating Area

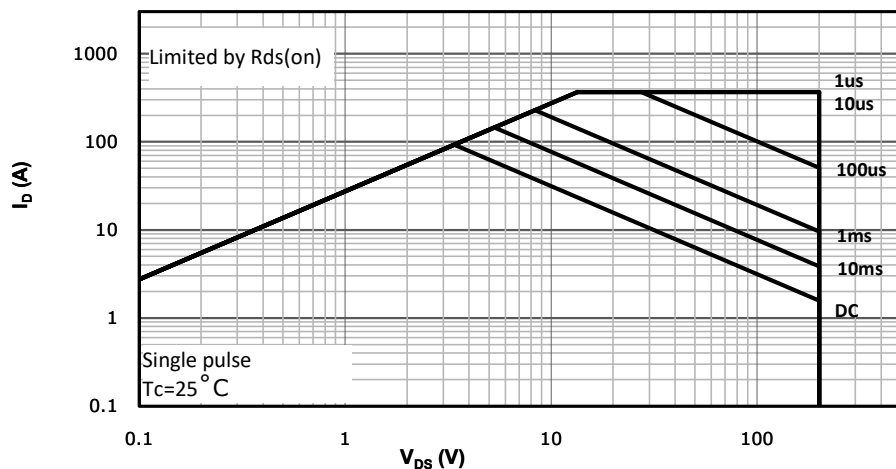
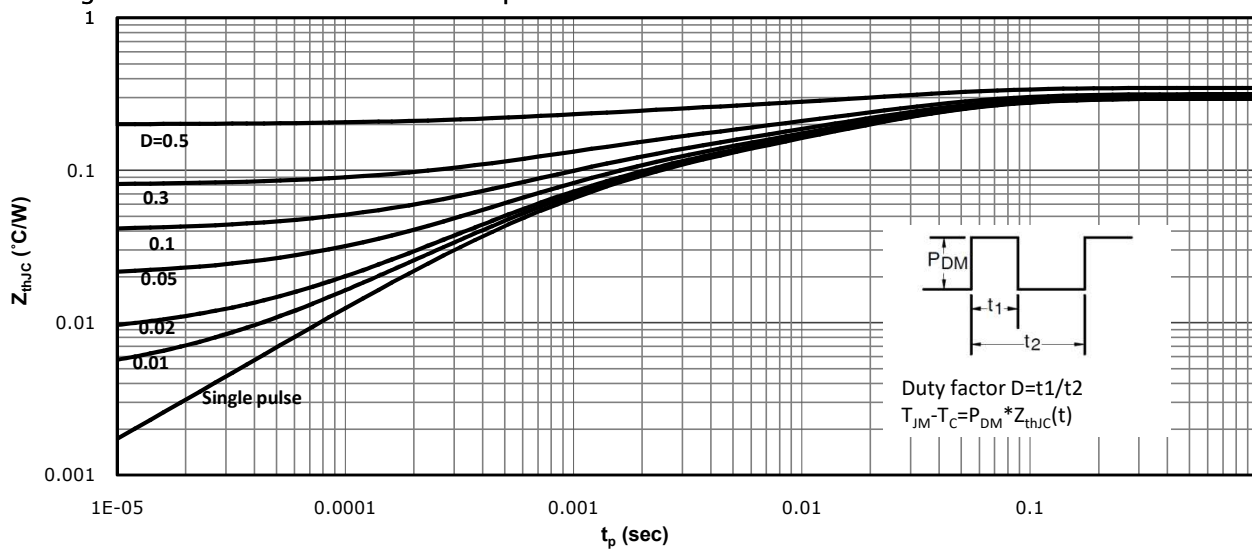
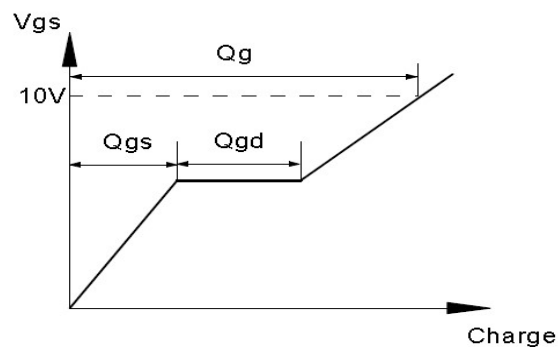
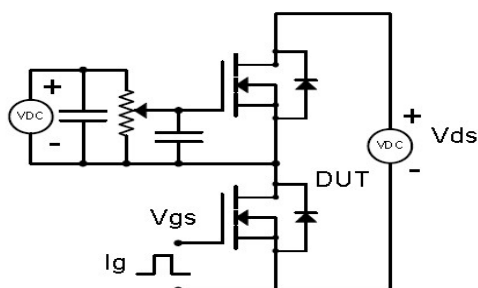


Fig 14: Max. Transient Thermal Impedance

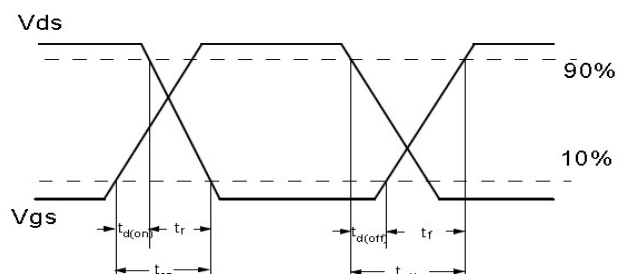
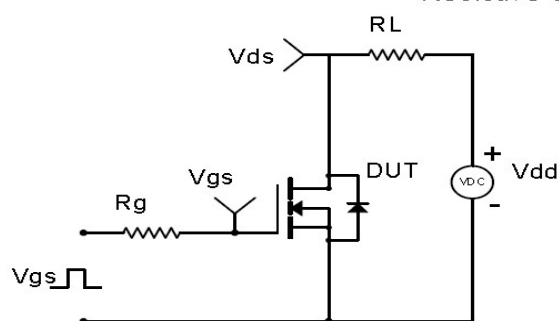


Test Circuit & Waveform

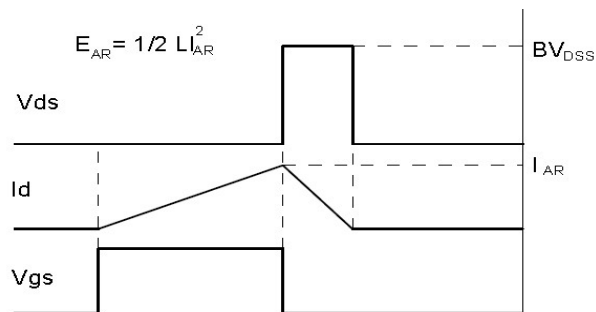
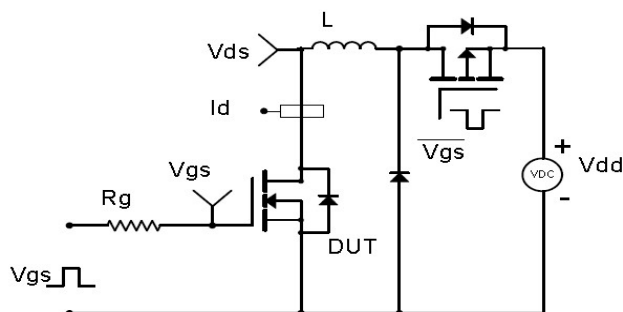
Gate Charge Test Circuit & Waveform



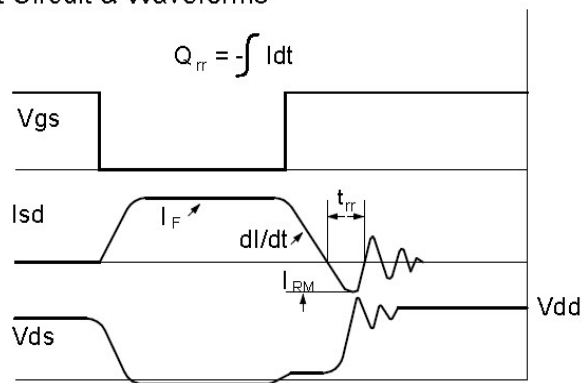
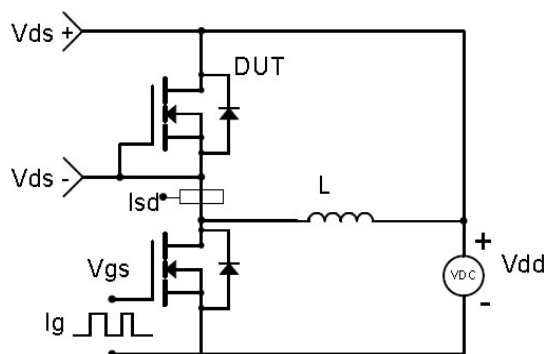
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

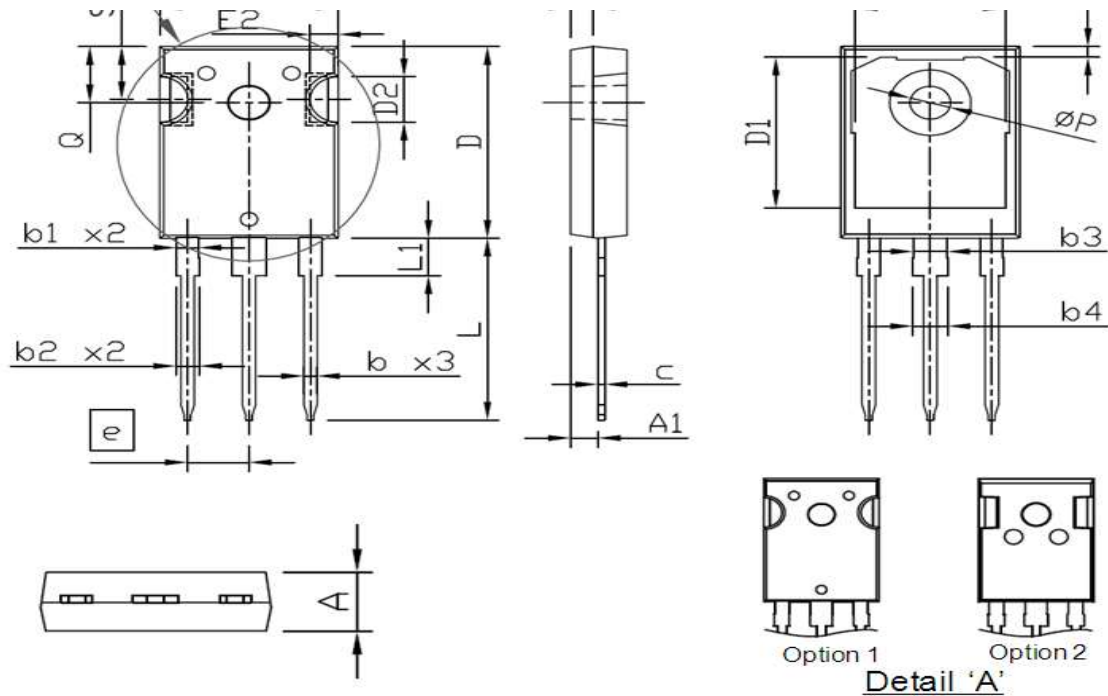


Diode Recovery Test Circuit & Waveforms



Package Outline: TO-247





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.85	5.15	0.191	0.203
A1	2.27	2.54	0.089	0.100
A2	1.90	2.10	0.075	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.16	0.075	0.085
b2	2.00	2.21	0.079	0.087
b3	2.87	3.13	0.113	0.123
b4	2.87	3.20	0.113	0.126
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	3.68	5.10	0.145	0.201
D3	0.95	1.35	0.037	0.053
e	5.44 BSC.		0.214 BSC.	
E	15.70	16.13	0.618	0.635
E1	13.03	14.15	0.513	0.557
E2	2.20	2.60	0.087	0.102
L	19.72	20.32	0.776	0.800
L1	4.00	4.47	0.157	0.176
Q	6.04	6.30	0.238	0.248
P	3.50	3.70	0.138	0.146
S	5.49	6.00	0.216	0.236

Revision History

Revision	Date	Major changes
1.0	2021/9/3	Release of Preliminary version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.